

MICROWAVE POWER GaAs FET

TIM6472-30UL

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- ·BROAD BAND INTERNALLY MATCHED FET
- -HIGH POWER

P1dB= 45.0dBm at 6.4GHz to 7.2GHz

·HIGH GAIN

G1dB= 9.5dB at 6.4GHz to 7.2GHz

·HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 6.4A f = 6.4 to 7.2GHz	dBm	44.0	45.0	_
Power Gain at 1dB Gain Compression Point	G1dB		dB	8.5	9.5	_
Drain Current	IDS1		Α	_	7.0	8.0
Gain Flatness	ΔG		dB	_	_	±0.6
Power Added Efficiency	ηadd		%		40	_
3rd Order Intermodulation Distortion	IM3	Two Tone Test Po= 34.0dBm, Δ f= 5MHz (Single Carrier Level)	dBc	-44	-47	_
Drain Current	IDS2		Α	_	7.0	8.0
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C	_	_	100

Recommended Gate Resistance(Rg): 28 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 10.0A	S	_	8.0	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 80mA	V	-0.5	-2.0	-3.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	А	_	16.0	_
Gate-Source Breakdown Voltage	VGSO	IGS= -240μA	V	-5		
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	1.0	1.5

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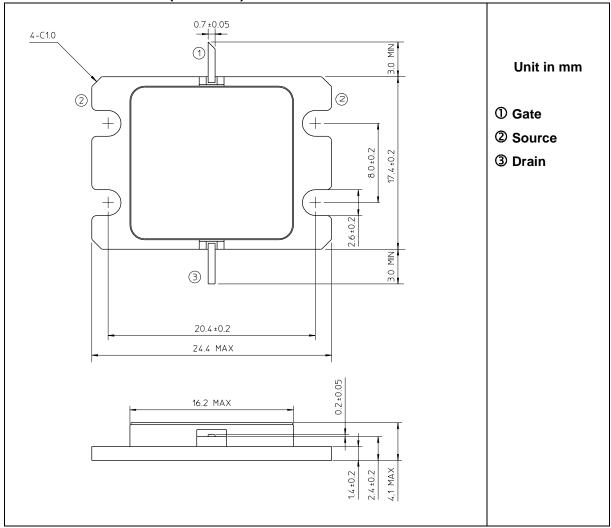


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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	18.0
Total Power Dissipation (Tc= 25°C)	PT	W	100
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (7-AA05A)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.